



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 5.0V$	340mA
007	2.5Ω @ V _{GS} = 2.5V	300mA

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications:

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

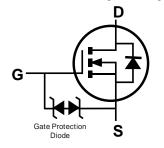
Mechanical Data

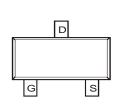
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 63
- Weight: 0.006 grams (Approximate)





SOT323





Top View

Equivalent Circuit

Top View

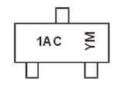
Ordering Information (Note 4)

-		
Part Number	Case	Packaging
DMN61D9UWQ-7	SOT323	3,000/Tape & Reel
DMN61D9UWQ-13	SOT323	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1AC= Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	E	ı	F	G	Н			J	K	L	-	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	60	V			
Gate-Source Voltage	V_{GSS}	±20	V			
Continuous Drain Current (Note 7) V F 0V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	340 270	mA	
Continuous Drain Current (Note 7) V _{GS} = 5.0V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	400 300	mA	
Maximum Continuous Body Diode Forward Current	Is	0.4	Α			
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 7)	I _{DM}	1.2	A		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		393	°C/W
Internal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	306	C/VV
Total Power Dissipation (Note 7)		P_{D}	440	mW
Thermal Resistance, Junction to Ambient (Note 7)	Steady State		289	°C/W
Internal Resistance, Junction to Ambient (Note 1)	t<5s	$R_{\theta JA}$	235	C/VV
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

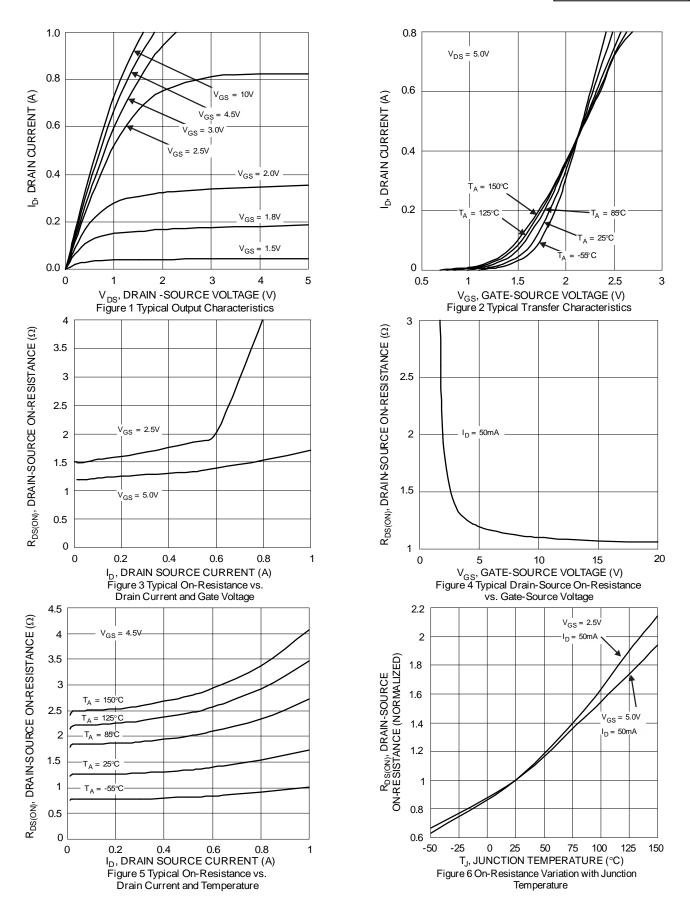
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 5.0V, I_D = 0.05A$
Static Drain-Source On-Resistance	R _{DS(ON)}		1.6	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
1			2.5	3.5		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}	_	0.75	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	28.5	_	рF	
Output Capacitance	Coss	_	3.9	_	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.5	_	pF	1 = 1.0W112
Gate Resistance	R_g	_	65	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qq	_	0.4	_	nC	451414 4014
Gate-Source Charge	Q _{qs}	_	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q_{qd}	_	0.1	_	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	_	2.1	_	ns	
Turn-On Rise Time	t _R	_	1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	14.4	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$
Turn-Off Fall Time	t _F	_	8.4	_	ns	

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







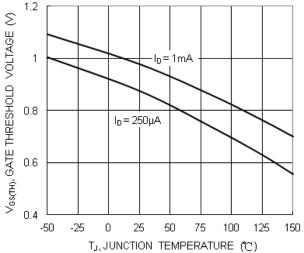
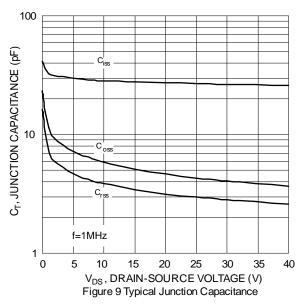
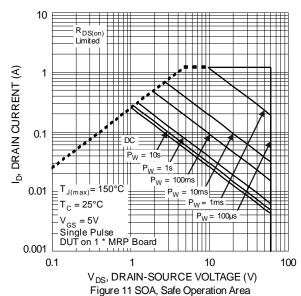
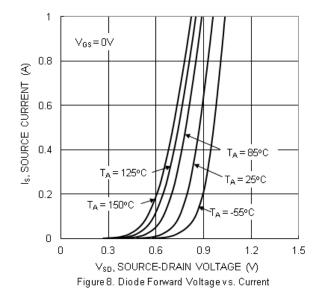
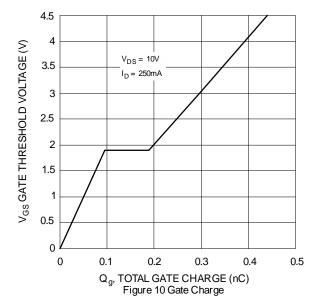


Figure 7. Gate Threshold Variation vs. Junction Temperature

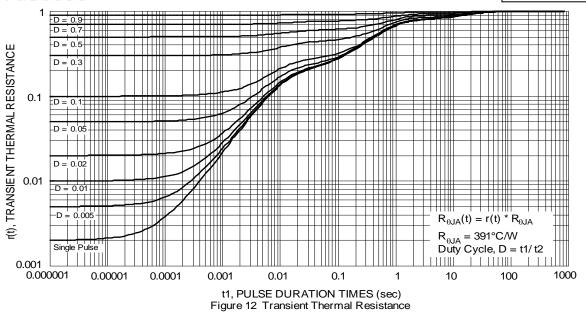






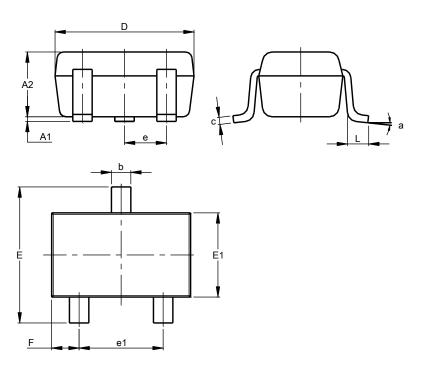






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

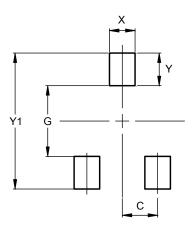


SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	().650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)				
С	0.650				
G	1.300				
X	0.470				
Y	0.600				
Y1	2.500				

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